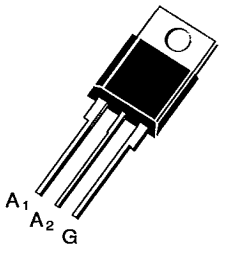
SGS-THOMSON MICROELECTRONICS

S G S-THOMSON

# BTA/BTB 10 B

## TRIACS

- GLASS PASSIVATED CHIP
- EXCELLENT $(dv/dt)_c > 10$ V/µs
- $I_{GT}$ SPECIFIED IN FOUR QUADRANTS
- AVAILABLE IN INSULATED VERSION → BTA SERIES (INSULATING VOLTAGE 2500 $V_{RMS}$) OR IN UNINSULATED VERSION → BTB SERIES
- UL RECOGNIZED FOR BTA SERIES (E81734)




**TO 220 AB**
(Plastic)

### DESCRIPTION

New range suited for applications such as phase control and static switching.

### ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | | Value | Unit |
|---|---|---|---|---|
| $I_{T(RMS)}$ | RMS on-state Current (360° conduction angle) | $T_C$ = 75 °C | 10 | A |
| $I_{TSM}$ | Non Repetitive Surge Peak on-state Current ($T_j$ initial = 25 °C - Half sine wave) | t = 8.3 ms | 105 | A |
| | | t = 10 ms | 100 | |
| $I^2t$ | $I^2t$ Value for Fusing | t = 10 ms | 50 | $A^2s$ |
| di/dt | Critical Rate of Rise of on-state Current (1) | Repetitive F = 50 Hz | 10 | A/µs |
| | | Non Repetitive | 50 | |
| $T_{stg}$<br>$T_j$ | Storage and Operating Junction Temperature Range | | − 40 to 150<br>− 40 to 110 | °C<br>°C |

| Symbol | Parameter | BTA/BTB 10– | | | | | Unit |
|---|---|---|---|---|---|---|---|
| | | 200B | 400B | 600B | 700B | 800B | |
| $V_{DRM}$ | Repetitive Peak off-state Voltage (2) | 200 | 400 | 600 | 700 | 800 | V |

(1) $I_G$ = 1 A $di_G/dt$ = 1 A/µs
(2) $T_j$ = 110 °C.

### THERMAL RESISTANCES

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $R_{th\ (j-a)}$ | Junction to Ambient | 60 | °C/W |
| $R_{th\ (j-c)}$ DC | Junction to Case for DC | 3.9 | °C/W |
| $R_{th\ (j-c)}$ AC | Junction to Case for 360 ° Conduction Angle (F = 50 Hz) | 2.9 | °C/W |

## GATE CHARACTERISTICS (maximum values)

$P_{GM}$ = 40 W ($t_p$ = 10 µs) $I_{GM}$ = 4 A ($t_p$ = 10 µs)
$P_{G(AV)}$ = 1 W $V_{GM}$ = 16 V ($t_p$ = 10 µs)

T-25-15

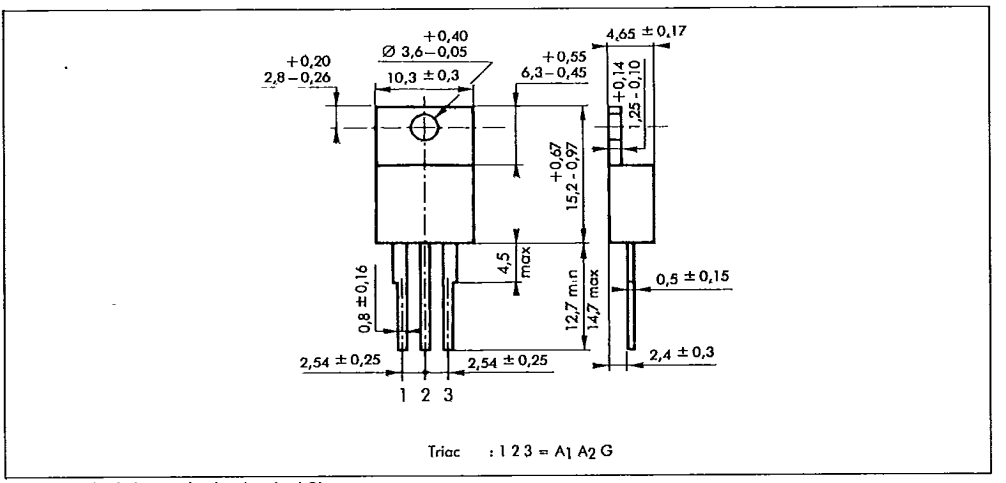
## ELECTRICAL CHARACTERISTICS

| Symbol | Test Conditions | | | Quadrants | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|---|---|
| $I_{GT}$ | $T_j$ = 25 °C $V_D$ = 12 V $R_L$ = 33 Ω<br>Pulse Duration > 20 µs | | | I-II-III | | | 50 | mA |
| | | | | IV | | | 100 | |
| $V_{GT}$ | $T_j$ = 25 °C $V_D$ = 12 V $R_L$ = 33 Ω<br>Pulse Duration > 20 µs | | | I-II-III-IV | | | 1.5 | V |
| $V_{GD}$ | $T_j$ = 110 °C | $V_D = V_{DRM}$ | $R_L$ = 3.3 kΩ | I-II-III-IV | 0.2 | | | V |
| $I_H$* | $T_j$ = 25 °C | $I_T$ = 100 mA | Gate Open | | | | 50 | mA |
| $I_L$ | $T_j$ = 25 °C $V_D$ = 12 V $I_G$ = 200 mA<br>Pulse Duration > 20 µs | | | I-III-IV | | 50 | | mA |
| | | | | II | | 100 | | |
| $V_{TM}$* | $T_j$ = 25 °C | $I_{TM}$ = 14 A | $t_p$ = 10 ms | | | | 1.5 | V |
| $I_{DRM}$* | $V_{DRM}$ Specified | | $T_j$ = 25 °C | | | | 0.01 | mA |
| | | | $T_j$ = 110 °C | | | | 0.5 | |
| dv/dt* | $T_j$ = 110 °C Gate Open<br>Linear Slope up to $V_D$ = 67 % $V_{DRM}$ | | | | 250 | 500 | | V/µs |
| $(dv/dt)_c$* | $T_C$ = 75 °C $V_D = V_{DRM}$ $I_T$ = 14 A<br>$(di/dt)_c$ = 4.4 A/ms | | | | 10 | | | V/µs |
| $t_{gt}$ | $T_j$ = 25 °C $V_D = V_{DRM}$ $I_T$ = 14 A<br>$I_G$ = 80 mA $di_G/dt$ = 1 A/µs | | | I-II-III-IV | | 2 | | µs |

* For either polarity of electrode $A_2$ voltage with reference to electrode $A_1$.

## PACKAGE MECHANICAL DATA

TO 220 AB Plastic




Cooling method : by conduction (method C)
Marking : type number
Weight : 2 g.

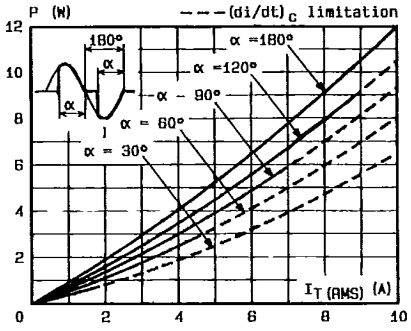



Fig.1 - Maximum mean power dissipation versus RMS on-state current (F = 60 Hz).

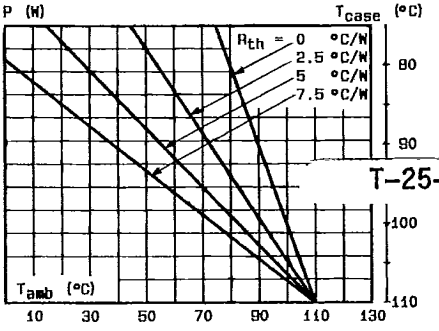



Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures ($T_{amb}$ and $T_{case}$) for different thermal resistances heatsink + contact.

T-25-15

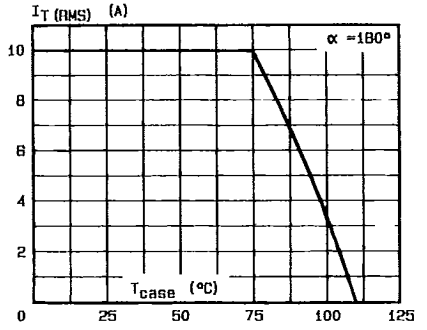



Fig.3 - RMS on-state current versus case temperature.

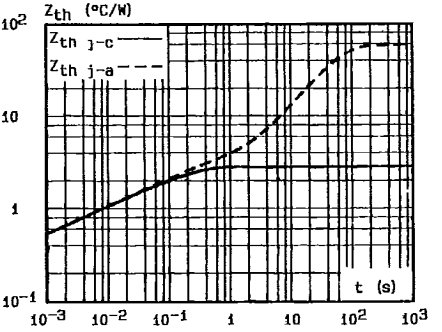



Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

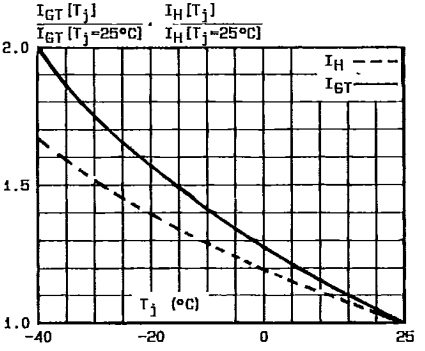



Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

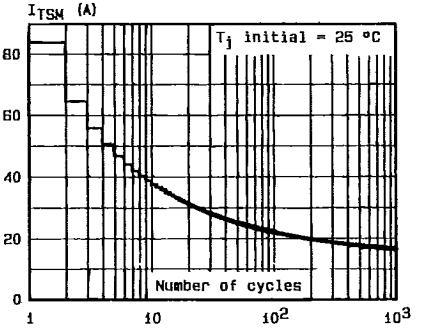



Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

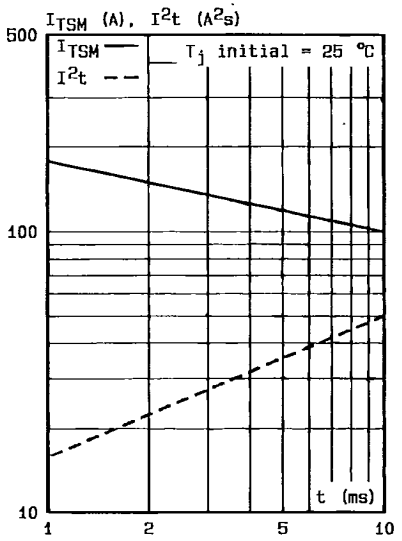



Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : t ≤ 10 ms, and corresponding value of $I^2t$.

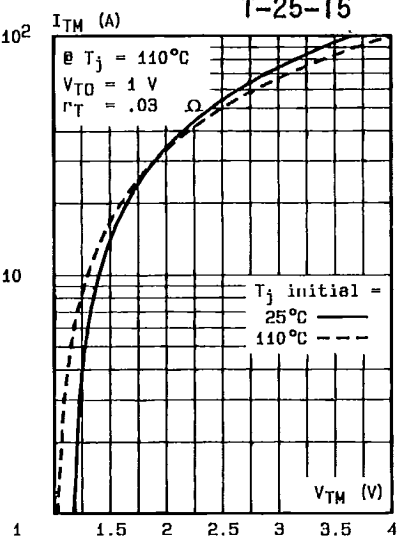



Fig.8 - On-state characteristics (maximum values).